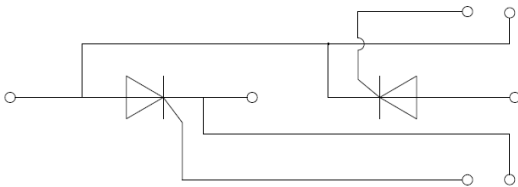




°C		



	°C			
				°C
				°C



	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
		V				

			±		

FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)

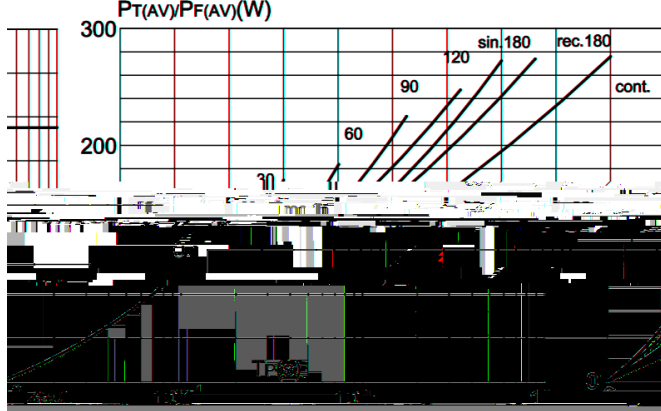


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)

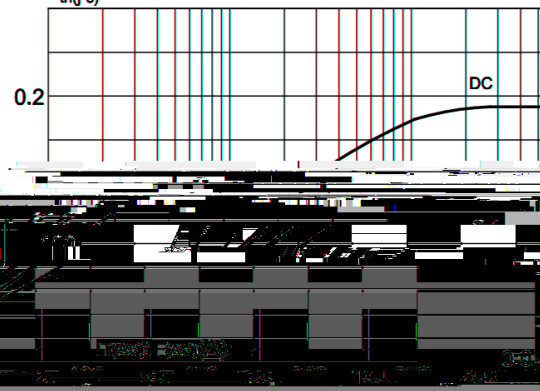


FIG.5 Gate trigger characteristics

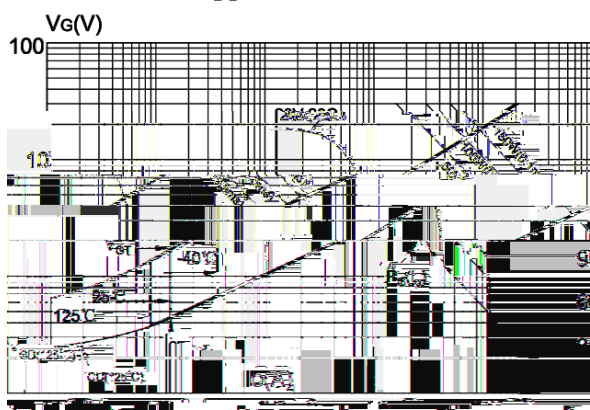


FIG.6: Forward current vs. case temperature
 $I_{F(AV)}$ (A) (per thyristor or diode)

